

**Amendments to the Specification:**

Please replace paragraph [0034] with the following rewritten paragraph:

[0034] An aperture 12, which communicates with the through hole 4 via a dielectric film 10, is formed in the electrode 2. The conduction layer 8 is formed in ~~stacked~~stacked layers at least on a part of the electrode 2, and a part thereof defines a connection section 14 that is electrically connected to the exterior. Within the through ~~hole 4~~, hole 4, the dielectric film 10 is formed below the conduction layer 8, to thereby shut out the electrical connection to integrated circuits that are formed within the base 6. Further, the conduction layer 8 provides electrical connection between the non-active surface A and the active surface B of the base 6.

Please replace paragraph [0077] with the following rewritten paragraph:

[0077] The semiconductor device 1 is manufactured in the following manner. First, each of the semiconductor chip forming sections 3 of the semiconductor wafer 5, shown in Fig. 1, is subject to electric characteristic examination using an LSI tester and a wafer ~~prober~~probe to determine whether it is good or bad. "BAD" marks 3a are noted on bad semiconductor chip forming sections, as shown in Fig. 2. "BAD" marks 3a may be marked by a method using ink or laser, or a wafer map (data representative of good products or bad products stored by a computer).

Please replace paragraph [0103] with the following rewritten paragraph:

[0103] Also, in the example described above in the fourth embodiment, the active surface "b" of the other segmented semiconductor chip 9 is laid over the other semiconductor chip 6b that is formed of a good segmented product in the second semiconductor wafer, and they are electrically connected to one another by the bumps 101. However, without being limited to this example, for example, a non-active surface of ~~another one~~another one segmented semiconductor chip may be affixed to another semiconductor chip, that is formed of a good segmented product taken from a second semiconductor wafer by a die-bond agent, and electrodes on an active surface of the other segmented semiconductor chip and electrodes on the side of the other semiconductor chip, that is formed of the good segmented product taken from the second semiconductor wafer, are connected to one another by ~~wiring~~wire bondings, and a protection layer to protect the ~~wiring~~wire bonding sections may be provided.